Xianglong Li

List of Publications by Year
in descending order

11 papers	70 citations	1684188 5 h-index	1720034 7 g-index
11 all docs	11 docs citations	11 times ranked	34 citing authors

#	Article	IF	Citations
1	Improved MEOL and BEOL Parasitic-Aware Design Technology Co-Optimization for 3 nm Gate-All-Around Nanosheet Transistor. IEEE Transactions on Electron Devices, 2022, 69, 462-468.	3.0	0
2	Vertically Stacked Nanosheets Tree-Type Reconfigurable Transistor With Improved ON-Current. IEEE Transactions on Electron Devices, 2022, 69, 370-374.	3.0	16
3	Impact of Process Fluctuations on RF Small-Signal Parameter of Gate-All-Around Nanosheet Transistor Beyond 3 nm Node. IEEE Transactions on Electron Devices, 2022, 69, 31-38.	3.0	5
4	Impact of Process Variation on Nanosheet Gate-All-Around Complementary FET (CFET). IEEE Transactions on Electron Devices, 2022, 69, 4029-4036.	3.0	11
5	Impact of Process Fluctuations on Reconfigurable Silicon Nanowire Transistor. IEEE Transactions on Electron Devices, 2021, 68, 885-891.	3.0	13
6	Performance Evaluation of Negative Capacitance Reconfigurable Field Effect Transistor for Sub 10 nm Integration. , 2021, , .		1
7	Evaluation of total-ionizing-dose effects on reconfigurable field effect transistors and SRAM circuits. Semiconductor Science and Technology, 2021, 36, 085011.	2.0	1
8	Enhanced logic gates and SRAM based on reconfigurable field-effect transistor with asymmetric spacer engineering. Semiconductor Science and Technology, 2021, 36, 115002.	2.0	0
9	Analysis of Metal Work-Function Modulation Effect in Reconfigurable Field-Effect Transistor. IEEE Transactions on Electron Devices, 2020, 67, 3745-3752.	3.0	5
10	Electronic Assessment of Novel Arch-Shaped Asymmetrical Reconfigurable Field-Effect Transistor. IEEE Transactions on Electron Devices, 2020, 67, 1894-1901.	3.0	11
11	Investigation of process variation in vertically stacked gate-all-around nanowire transistor and SRAM circuit. Semiconductor Science and Technology, 0, , .	2.0	7